IN THE CLAIMS:

Please amend Claims 3 and 4 as shown below. The claims, as pending in the subject application, read as follows:

1. (Original) A field effect transistor comprising an organic semiconductor layer comprising a compound having a monobenzoporphyrin skeleton represented by the general formula (1):

wherein R_1 and R_2 are independently selected from the group consisting of a hydrogen atom, a halogen atom, a hydroxyl group, and alkyl, alkenyl, oxyalkyl, thioalkyl, alkyl ester and aryl groups each having 1 to 12 carbon atoms with the proviso that adjacent R_1 may be the same or different and adjacent R_2 may be the same or different and that at least two of R_2 are not hydrogen atoms; R_3 is a hydrogen atom or an aryl group; and M denotes two hydrogen atoms, a metal atom or a metal oxide.

2. (Original) The field effect transistor according to claim 1, wherein the organic semiconductor layer has at least one peak at Bragg angle (20) $7.8^{\circ} \pm 0.2^{\circ}$ in terms of Cu K-alpha X-ray diffraction.

- 3. (Currently Amended) The field effect transistor according to claim 1 or 2, wherein R_1 and R_3 of the monobenzoporphyrin compound represented by the general formula (1) are hydrogen atoms and at least two of R_2 are alkyl groups having 1 to 12 carbon atoms.
- 4. (Currently Amended) The field effect transistor according to any one of claims 1 to 3 claim 1, wherein M of the monobenzoporphyrin compound represented by the general formula (1) is two hydrogen atoms or one copper atom.
- 5. (Original) A method of producing a field effect transistor, which comprises the step of heating a monobicycloporphyrin compound represented by the general formula (2):

wherein R_1 , R_2 and R_4 are independently selected from the group consisting of a hydrogen atom, a halogen atom, a hydroxyl group, and alkyl, alkenyl, oxyalkyl, thioalkyl, alkyl ester, and aryl groups each having 1 to 12 carbon atoms with the proviso that adjacent R_1 may be the same or different and adjacent R_2 may be the same or different and that at least two of R_2 are not hydrogen atoms; R_3 is a hydrogen atom or an aryl group; and M denotes two hydrogen atoms, a metal atom or a metal oxide, to effect conversion to a monobenzoporphyrin compound represented by the general formula (1):

wherein R₁, R₂, R₃, and M are as above defined.

- 6. (Original) The method of producing a field effect transistor according to claim 5, wherein the monobicycloporphyrin compound represented by the general formula (2) is heated at a temperature between 130°C to 250°C to be converted to the monobenzoporphyrin compound represented by the general formula (1).
- 7. (Original) A field effect transistor comprising an organic semiconductor layer comprising a compound having a monobenzoporphyrin skeleton and having at least one peak at Bragg angle (2 θ) 7.8° \pm 0.2° in terms of Cu K-alpha X-ray diffraction.